IS852
IS852X

HIGH VOLTAGE DARLINGTON OUTPUT OPTICALLY COUPLED ISOLATOR

APPROVALS

- UL recognised, File No. E91231

'X' SPECIFICATION APPROVALS

- VDE 0884 in 3 available lead form : -
  - STD
  - G form
  - SMD approved to CECC 00802
- BSI approved - Certificate No. 8001

DESCRIPTION

The IS852 is an optically coupled isolator consisting of infrared light emitting diode and a high voltage NPN silicon photo darlington which has an integral base-emitter resistor to optimise switching speed and elevated temperature characteristics in a standard 4 pin dual in line plastic package.

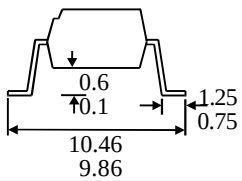
FEATURES

- Options :-
  10mm lead spread - add G after part no.
  Surface mount - add SM after part no.
  Tape&reel - add SMT&R after part no.
- High Isolation Voltage ($5.3kV_{RMS}$,$7.5kV_{PK}$)
- High Current Transfer Ratio (1000% min)
- High BV_{CEO} (300V min.)
- Low input current 1mA I_F

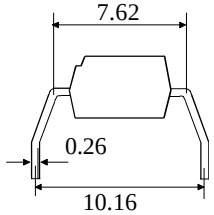
APPLICATIONS

- Modems
- Copiers, facsimiles
- Numerical control machines
- Signal transmission between systems of different potentials and impedances

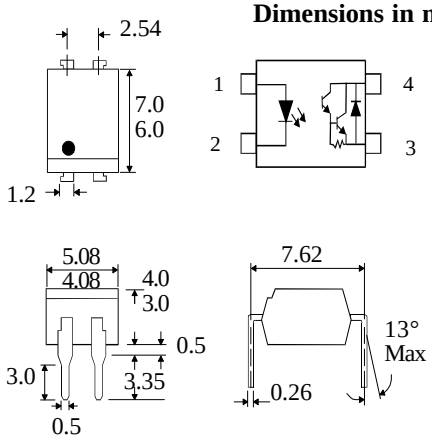
OPTION SM
SURFACE MOUNT



OPTION G



Dimensions in mm



ABSOLUTE MAXIMUM RATINGS (25°C unless otherwise specified)

Storage Temperature	-55°C to + 125°C
Operating Temperature	-30°C to + 100°C
Lead Soldering Temperature (1/16 inch (1.6mm) from case for 10 secs)	260°C

INPUT DIODE

Forward Current	50mA
Reverse Voltage	6V
Power Dissipation	70mW

OUTPUT TRANSISTOR

Collector-emitter Voltage BV_{CEO}	300V
Emitter-collector Voltage BV_{ECO}	0.1V
Collector Current I_C	150mA
Power Dissipation	150mW

POWER DISSIPATION

Total Power Dissipation	200mW

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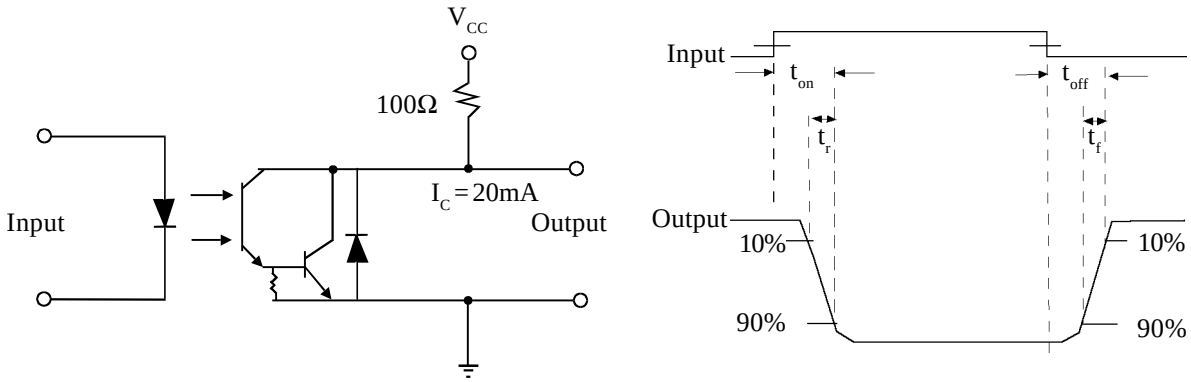
ELECTRICAL CHARACTERISTICS (T_A= 25°C Unless otherwise noted)

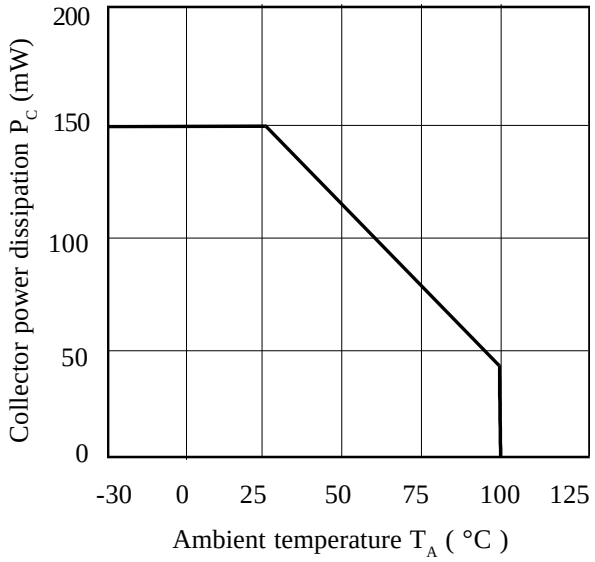
PARAMETER			MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V_F)			1.2	1.4	V	I_F = 10mA
	Reverse Current (I_R)				10	µA	V_R = 4V
Output	Collector-emitter Breakdown (BV_{CEO})		300			V	I_C = 0.1mA
	Emitter-collector Breakdown (BV_{ECO})		0.1			V	I_E = 10µA
	Collector-emitter Dark Current (I_{CEO})			10	200	nA	V_{CE} = 200V
Coupled	Current Transfer Ratio (CTR)		1000	4000	15000	%	1mA I_F, 2V V_{CE}
	Collector-emitter Saturation Voltage $V_{CE(SAT)}$				1.2	V	20mA I_F, 100mA I_C
	Input to Output Isolation Voltage V_{ISO}		5300 7500			V_{RMS} V_{PK}	See note 1 See note 1
	Input-output Isolation Resistance R_{ISO}		$5x10^{10}$			Ω	V_{IO} = 500V (note 1)
	Input-output Capacitance	Cf			1	pF	V = 0, f = 1MHz
	Cut-off Frequency	fc		7		kHz	V_{Ce} = 2V, I_C = 20mA, R_L = 100Ω, –3dB
	Output Rise Time Output Fall Time	tr tf		100 20	300 100	µs µs	V_{Ce} = 2V, I_C = 20mA, R_L = 100Ω

Note 1 Measured with input leads shorted together and output leads shorted together.
Note 2 Special Selections are available on request. Please consult the factory.

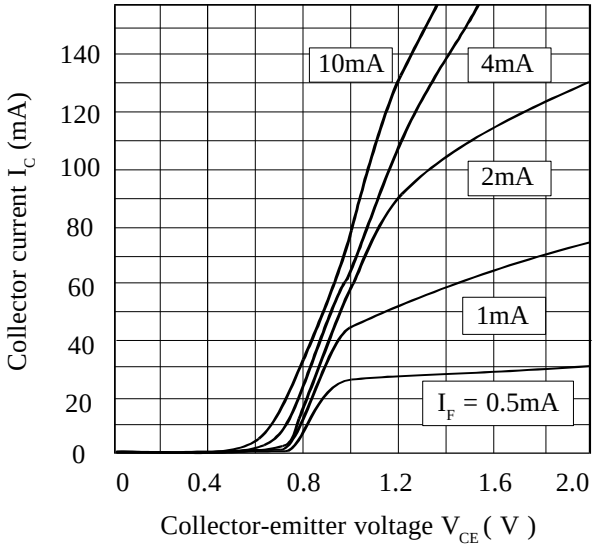
FIGURE 1



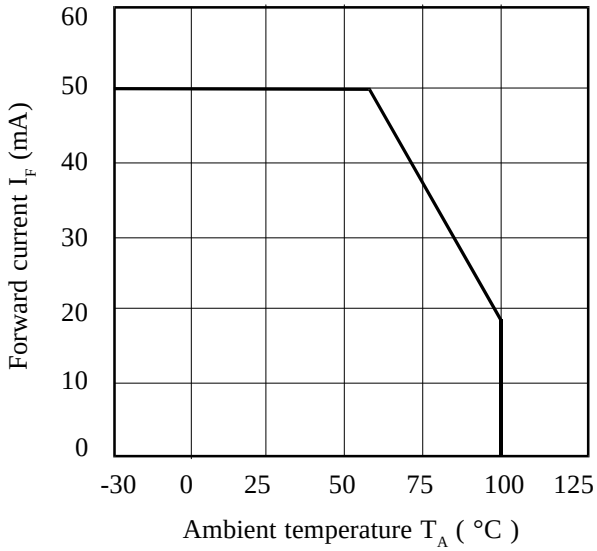
Collector Power Dissipation vs. Ambient Temperature



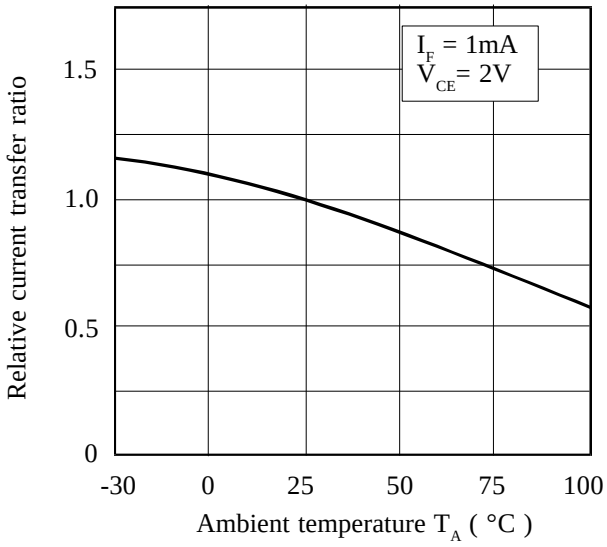
Collector Current vs. Collector-emitter Voltage



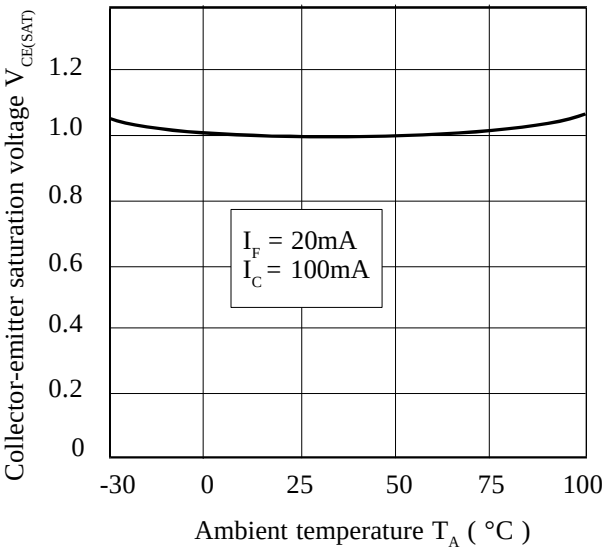
Forward Current vs. Ambient Temperature



Relative Current Transfer Ratio vs. Ambient Temperature



Collector-emitter Saturation Voltage vs. Ambient Temperature



Collector Dark Current vs. Ambient Temperature